

NTE56004 thru NTE56010 TRIAC, 15 Amp

The NTE56004 thru NTE56010 series of TRIACs are designed primarily for full—wave AC control applications, such as solid—state relays, motor controls, heating controls and power supplies; or wherever full—wave silicon gate controlled solid—state devices are needed. TRIAC type thyristors switch from a blocking to a conducting state for either polarity of applied anode voltage with positive or negative gate triggering.

Features:

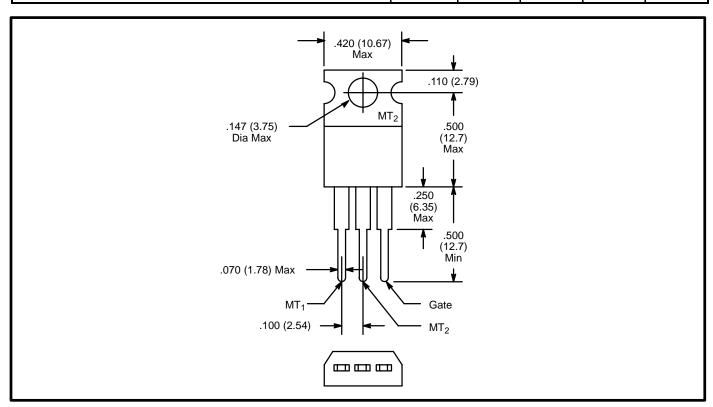
- Blocking Voltage from 200 to 800 Volts
- All Diffused and Glass Passivated Junctions
- Small, Rugged, TO220 package for Low Thermal Resistance, High Heat Dissipation and Durability
- Gate Triggering specified in Four Quadrants

Absolute Maximum Ratings:

Peak Repetitive Off–State Voltage, $(T_J = -40^\circ \text{ to } 125^\circ\text{C})$, V_{DRM}
NTE56004
NTE56006400V
NTE56008 600V
NTE56010800V
Peak Gate Voltage, V _{GM} 10V
On–State Current RMS (Full Cycle Sine Wave 50 to 60Hz, $T_C = +90^{\circ}C$), $I_{T(RMS)}$
Circuit Fusing (t = 8.3ms) I^2t 93 A^2s
Peak Surge Current (One Full Cycle, 60Hz, T _C = +80°C), I _{TSM}
Preceded and followed by rated current
Peak Gate Power ($T_C = +80^{\circ}C$, Pulse Width = 2μ s), P_{GM}
Average Gate Power ($T_C = +80^{\circ}C$, $t = 8.3$ ms), $P_{G(AV)}$
Peak Gate Current, I _{GM}
Operating Junction Temperature Range, T _J
Storage Temperature Range, T _{stg} 40° to +150°C
Thermal Resistance, Junction–to–Case, R _{thJC}

<u>Electrical Characteristics</u> ($T_C = 25^{\circ}C$, and either polarity of MT2 to MT1 Voltage, unless otherwise noted)

Characteristics	Symbol	Min	Тур	Max	Unit
Peak Forward or Reverse Blocking Current (Rated V _{DRM} , or V _{RRM} , Gate open) T _J =25°C T _J =125°C	I _{DRM} , I _{RRM}	_ _	_ _	10 2	μΑ mA
Peak On–State Voltage (I _{TM} = 21 A Peak; Pulse Width = 1 to 2ms, Duty Cycle ≤ 2%)	V _{TM}	_	1.3	1.6	Volts
Gate Trigger Current (Continuous dc)	I _{GT}			50 75	mA
	V _{GT}	- - - 0.2 0.2	0.9 1.1 1.4 -	2 2 2.5 - -	Volts
Holding Current (Either Direction) (V _D = 12Vdc, I _T = 200mA, Gate Open)	I _H	ı	6	40	mA
Turn–On Time (V _D = Rated V _{DRM} , I _{TM} = 17A) (I _{GT} = 120mA, Rise Time = 0.1μs, Pulse Width = 2μs)	t _{gt}	_	1.5	_	μs
Critical Rate of Rise of Commutation Voltage (V_D = Rated V_{DRM} , I_{TM} = 21 A, Commutating di/dt = 8A/ms, Gate Unenergized, T_C = 80°C)	dv/dt(c)	-	5	-	V/μs



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